

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1. (Original) A semiconductor device, comprising:
a thin film transistor formed on an insulating surface of a substrate; and
a diamond-like carbon film formed on a back surface of the substrate.
2. (Original) A semiconductor device according to claim 1, wherein the substrate is a quartz substrate.
3. (Original) A device according to claim 1, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ωcm .
4. (Original) A device according to claim 1, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.
5. (Original) A device according to claim 1, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.
6. (Original) A semiconductor device, comprising:
a diamond-like carbon film formed on an insulating surface of a substrate;
an underlayer film formed on the diamond-like carbon film; and
a thin film transistor formed on the underlayer film.
7. (Original) A device according to claim 6, wherein the substrate is a quartz substrate.

8. (Original) A device according to claim 6, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ωcm .

9. (Original) A device according to claim 6, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

10. (Original) A device according to claim 6, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

11. (Currently Amended) A semiconductor device, comprising:
a thin film transistor formed over a substrate having an insulating surface;
an interlayer insulating film formed over the thin film transistor; and
a diamond-like carbon film formed on the interlayer insulating film; and , wherein the
~~diamond like carbon film has a thickness of 5 to 100 nm~~
a pixel electrode formed over the diamond-like carbon film.

12. (Original) A device according to claim 11, further comprising a transparent conductive film formed over the diamond-like carbon film.

13. (Canceled)

14. (Original) A device according to claim 11, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ωcm .

15. (Original) A device according to claim 11, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

16. (Original) A device according to claim 11, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

17-32. (Canceled)

33. (Previously Presented) An electronic device comprising:
a thin film transistor formed over a first insulating surface of a substrate; and
a diamond-like carbon film formed over a second insulating surface of the substrate,
wherein the first insulating surface is opposite to the second insulating surface.

34. (Previously Presented) A device according to claim 33, wherein the substrate is a quartz substrate.

35. (Previously Presented) A device according to claim 33, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ωcm .

36. (Previously Presented) A device according to claim 33, wherein said electronic device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus comprising a recording medium, a digital camera, a front type projector, and a rear type projector.

37. (Previously Presented) An electronic device comprising:
a diamond-like carbon film formed over an insulating surface of the substrate;
an underlayer film formed on the diamond-like carbon film; and
a thin film transistor formed on the underlayer film.

38. (Previously Presented) A device according to claim 37, wherein the substrate is a quartz substrate.

39. (Previously Presented) A device according to claim 37, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ωcm .

40. (Previously Presented) A device according to claim 37, wherein said electronic device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus comprising a recording medium, a digital camera, a front type projector, and a rear type projector.

41-48. (Canceled)

49. (Previously Presented) A device according claim 1, further comprising a buffer layer having at least one of silicon, silicon carbide, and silicon nitride.

50. (Previously Presented) A device according claim 6, further comprising a buffer layer having at least one of silicon, silicon carbide, and silicon nitride.

51-54. (Canceled)

55. (Previously Presented) A device according claim 1, further comprising a buffer layer having a thickness of 80 to 200 nm.

56. (Previously Presented) A device according claim 6, further comprising a buffer layer having a thickness of 80 to 200 nm.

57-60. (Canceled)

61. (New) A semiconductor device, comprising:
a diamond-like carbon film formed over a substrate;
a transistor formed over the substrate.

62. (New) A semiconductor device according to claim 61, wherein the substrate is a quartz substrate.

63. (New) A device according to claim 61, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ωcm .

64. (New) A device according to claim 61, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

65. (New) A device according to claim 1, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.